

SWITCHING DIODE		SOT-323 Plastic-Encapsulate Diodes			
<p>SOT-323</p> <p>Marking :A7t</p>		<p>Features</p> <ul style="list-style-type: none"> • For high-speed switching applications • Connected in series 			
Maximum Ratings @Ta=25°C					
Parameter		Symbol	Limit	Unit	
Reverse Voltage		V_R	75	V	
Forward Current		I_F	150	mA	
Non-Repetitive Peak Forward Surge Current @t=8.3ms		I_{FSM}	2.0	A	
Power Dissipation		P_D	200	mW	
Thermal Resistance Junction to Ambient		$R_{\theta JA}$	625	°C/W	
Junction Temperature		T_J	150	°C	
Storage Temperature range		T_{STG}	-55~+150	°C	
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)					
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	75		V
Reverse voltage leakage current	I_{R1}	$V_R=75V$		2.5	μA
	I_{R2}	$V_R=25V$		25	nA
Forward voltage	V_F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R=0$ $f=1MHz$		2	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10mA$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$		4	ns

Typical Characteristics

